

2SB0950 (2SB950), 2SB0950A (2SB950A)

Silicon PNP epitaxial planar type darlington

For power amplification and switching

Complementary to 2SD1276 and 2SD1276A

■ Features

- High forward current transfer ratio h_{FE}
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0950	-60	V
	2SB0950A	-80	
Collector-emitter voltage (Base open)	2SB0950	-60	V
	2SB0950A	-80	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_C	-4	A
Peak collector current	I_{CP}	-8	A
Collector power dissipation	$T_a = 25^\circ\text{C}$	40	W
		2	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

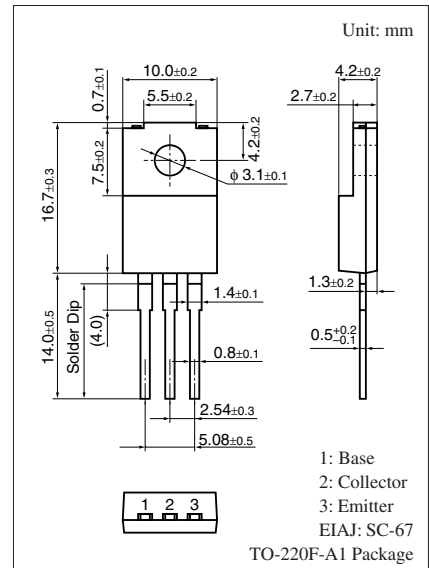
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0950	$I_C = -30\text{ mA}, I_B = 0$	-60			V
	2SB0950A		-80			
Base-emitter voltage	V_{BE}	$V_{CE} = -3\text{ V}, I_C = -3\text{ A}$			-2.5	V
Collector-base cutoff current (Emitter open)	2SB0950	$V_{CB} = -60\text{ V}, I_E = 0$			-200	μA
	2SB0950A		$V_{CB} = -80\text{ V}, I_E = 0$			
Collector-emitter cutoff current (Base open)	2SB0950	$V_{CE} = -30\text{ V}, I_B = 0$			-500	μA
	2SB0950A		$V_{CE} = -40\text{ V}, I_B = 0$			
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-2	mA
Forward current transfer ratio	h_{FE1}	$V_{CE} = -3\text{ V}, I_C = -0.5\text{ A}$	1000			—
	h_{FE2}^*		$V_{CE} = -3\text{ V}, I_C = -3\text{ A}$	1000		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = -3\text{ A}, I_B = -12\text{ mA}$			-2	V
	$V_{CE(sat)2}$	$I_C = -5\text{ A}, I_B = -20\text{ mA}$			-4	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}, f = 1\text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = -3\text{ A}, I_{B1} = -12\text{ mA}, I_{B2} = 12\text{ mA}$		0.3		μs
Storage time	t_{stg}	$V_{CC} = -50\text{ V}$		2		μs
Fall time	t_f			0.5		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	Q	P
h_{FE2}	1000 to 2500	2000 to 5000	4000 to 10000

Note) The part numbers in the parenthesis show conventional part number.



Internal Connection

